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## **RF Micro Devices(R) Expands High Power GaN Product Portfolio**

### **Highly-Efficient 140-Watt Transistor Released for Volume Production**

GREENSBORO, N.C., Oct 7, 2010 (GlobeNewswire via COMTEX News Network) -- RF Micro Devices, Inc. (Nasdaq:RFMD), a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies, today announced that RFMD(R) has qualified and production released the RF3934, a 140-watt highly-efficient gallium nitride (GaN) RF unmatched power transistor (UPT) with superior performance versus competing GaAs and silicon power technologies.

RFMD's unmatched power transistors support "green" architectures that reduce energy consumption, improving thermal management and network efficiency for network operators. The RF3934 operates over a broad frequency range (DC to 3GHz) in a single amplifier design. The high peak efficiency of >65% minimizes thermal management demand and improves overall power consumption requirements for end customers. Additionally, ease of design implementation and integration is enhanced through the incorporation of simple, optimized matching networks external to the package, providing wideband gain and power performance advantages in a single amplifier. The RF3934 is packaged in a hermetic, flanged ceramic two-leaded package that leverages RFMD's advanced heat sink and power dissipation technologies to deliver excellent thermal stability and conductivity.

Jeff Shealy, VP and general manager of RFMD's Defense and Power business unit, said, "The release of the RF3934 is an important milestone because it is the highest output power device in our UPT family. Furthermore, it is a key building block for our upcoming matched power transistor family, scheduled to be released later this fiscal year."

Bob Van Buskirk, President of RFMD's Multi-Market Products Group, said, "Our GaN products offer the added benefit of being produced in the same high volume manufacturing environment as our RFMD cellular products, which translates into industry-leading manufacturing cycle times. We further leverage our internal, high power packaging facility, with military and government security clearances, to enable flexible assembly and test strategies and short learning cycles to support important aerospace and defense programs."

The RF3934 is designed in RFMD's 48-volt high power-density GaN semiconductor process -- featuring a unique combination of high RF power density and efficiency, low capacitance and high thermal conductivity. Such features enable the development of compact and efficient high power amplifiers (HPAs) for a broad range of applications, including public mobile radio (PMR), 3G/4G wireless infrastructure, ISM (industrial scientific & medical), military and civilian radar and CATV transmission networks

The RF3934 is currently available for sampling and mass production. Product datasheets are available at [www.rfmd.com](http://www.rfmd.com)

#### About RFMD

RF Micro Devices, Inc. (Nasdaq:RFMD) is a global leader in the design and manufacture of high-performance semiconductor components. RFMD's products enable worldwide mobility, provide enhanced connectivity and support advanced functionality in the cellular handset, wireless infrastructure, wireless local area network (WLAN), CATV/broadband and aerospace and defense markets. RFMD is recognized for its diverse portfolio of semiconductor technologies and RF systems expertise and is a preferred supplier to the world's leading mobile device, customer premises and communications equipment providers.

The RF Micro Devices, Inc. logo is available at <http://www.globenewswire.com/newsroom/prs/?pkgid=6436>

Headquartered in Greensboro, N.C., RFMD is an ISO 9001- and ISO 14001-certified manufacturer with worldwide engineering, design, sales and service facilities. RFMD is traded on the NASDAQ Global Select Market under the symbol RFMD. For more information, please visit RFMD's web site at [www.rfmd.com](http://www.rfmd.com).

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and

performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including variability in operating results, risks associated with the impact of global macroeconomic and credit conditions on our business and the business of our suppliers and customers, our reliance on a few large customers for a substantial portion of our revenue, the rate of growth and development of wireless markets, our ability to bring new products to market, our reliance on inclusion in third party reference designs for a portion of our revenue, our ability to manage channel partner and customer relationships, risks associated with the operation of our wafer fabrication, molecular beam epitaxy, assembly and test and tape and reel facilities, our ability to complete acquisitions and integrate acquired companies, including the risk that we may not realize expected synergies from our business combinations, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, raw material costs and availability, our ability to reduce costs and improve margins in response to declining average selling prices, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on gallium arsenide (GaAs) for the majority of our products, dependence on third parties, and substantial reliance on international sales and operations. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K and other reports and statements filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

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SOURCE: RF Micro Devices

CONTACT: RF Micro Devices  
Doug DeLieto, VP, Investor Relations  
336-678-7088

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